IXYS

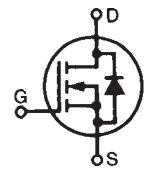
X3-Class HiPerFET™ Power MOSFET

IXFP36N20X3M

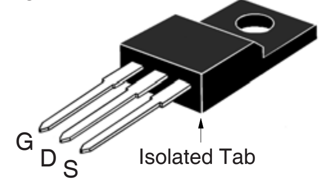
V_{DSS} = 200V
I_{D25} = 36A
$R_{DS(on)}$ ≤ 45mΩ

(Electrically Isolated Tab)

N-Channel Enhancement Mode



OVERMOLDED TO-220



G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	200	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	200	V
V_{GSS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C, Limited by T_{JM}	36	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	50	A
I_A	T_C = 25°C	18	A
E_{AS}	T_C = 25°C	300	mJ
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	20	V/ns
P_D	T_C = 25°C	36	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
V_{ISOL}	50/60 Hz, 1 Minute	2500	V~
M_d	Mounting Torque	1.13 / 10	Nm/lb.in
Weight		2.5	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.
BV_{DSS}	V_{GS} = 0V, I_D = 250μA	200		V
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 500μA	2.5		4.5 V
I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100 nA
I_{DSS}	V_{DS} = V_{DSS}, V_{GS} = 0V			5 μA
	T_J = 125°C			100 μA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 18A, Note 1		38	45 mΩ

Features

- International Standard Package
- Plastic Overmolded Tab
- Low $R_{DS(ON)}$ and Q_G
- Avalanche Rated
- 2500V~ Electrical Isolation
- Low Package Inductance

Advantages

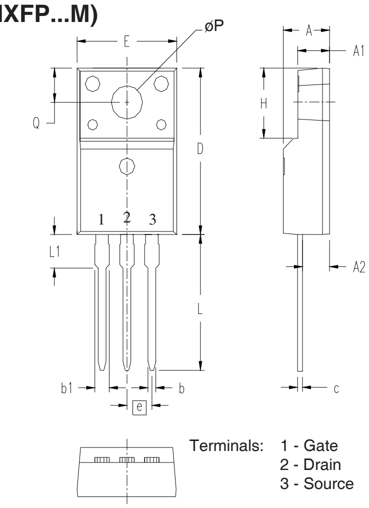
- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Min.	Typ.	Max	
g_{fs}	V_{DS} = 10V, I_D = 18A, Note 1	16	26		S
R_{Gi}	Gate Input Resistance		1.6		Ω
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		1425		pF
C_{oss}			280		pF
C_{rss}			1.2		pF
	Effective Output Capacitance				
$C_{o(er)}$	Energy related; V_{GS} = 0V, V_{DS} = 0.8 • V_{DSS}		130		pF
$C_{o(tr)}$	Time related		400		pF
$t_{d(on)}$	**Resistive Switching Times** V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 18A, R_G = 30Ω (External)		19		ns
t_r			30		ns
$t_{d(off)}$			54		ns
t_f			20		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 18A		21		nC
Q_{gs}			8		nC
Q_{gd}			7		nC
R_{thJC}				3.5	°C/W
R_{thCS}			0.50		°C/W

OVERMOLDED TO-220 (IXFP...M)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
ØP	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Min.	Typ.	Max	
I_S	V_{GS} = 0V			36	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			144	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.4	V
t_{rr}	I_F = 18A, -di/dt = 100A/μs, V_R = 100V		75		ns
Q_{RM}			230		nC
I_{RM}			6		A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

Fig. 1. Output Characteristics @ $T_J = 25^oC$

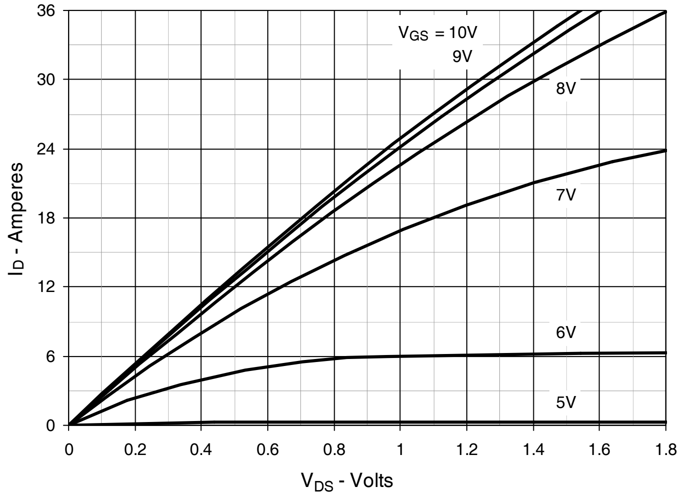


Fig. 2. Extended Output Characteristics @ $T_J = 25^oC$

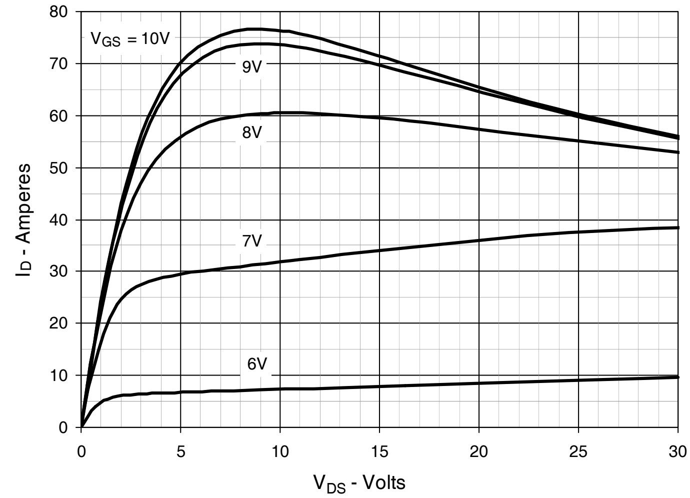


Fig. 3. Output Characteristics @ $T_J = 125^oC$

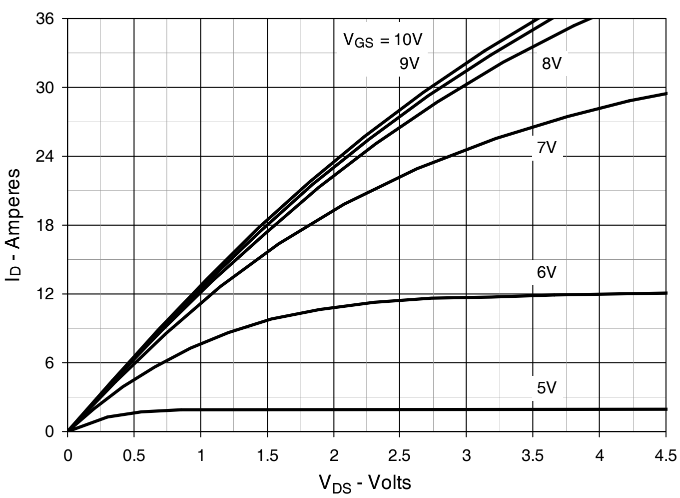


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 18A Value vs. Junction Temperature

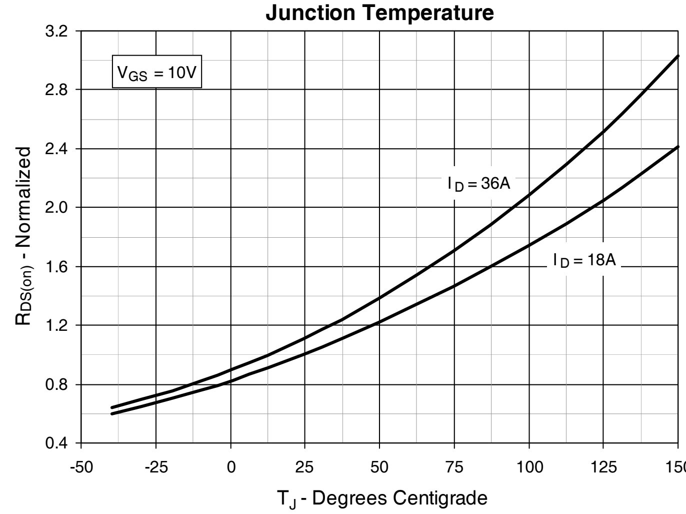


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 18A Value vs. Drain Current

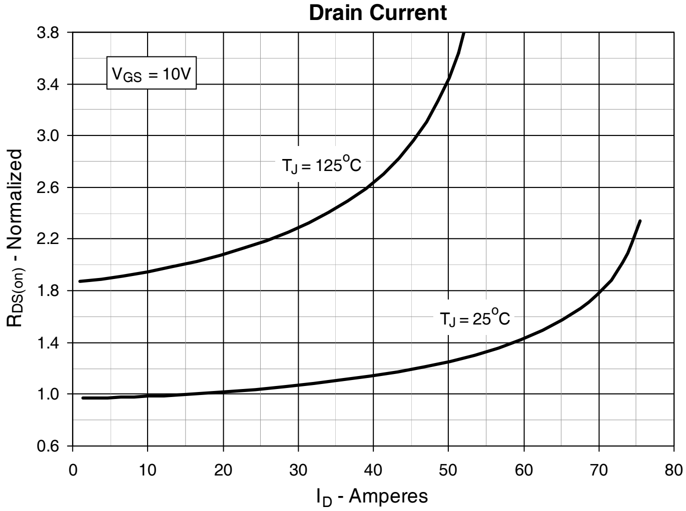


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

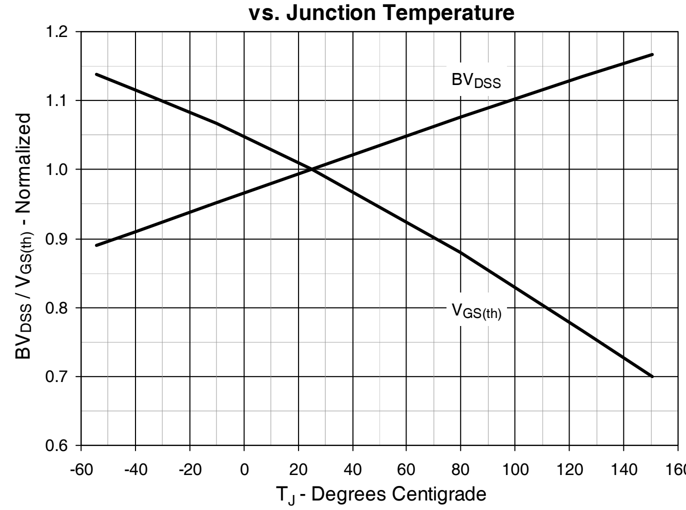


Fig. 7. Input Admittance

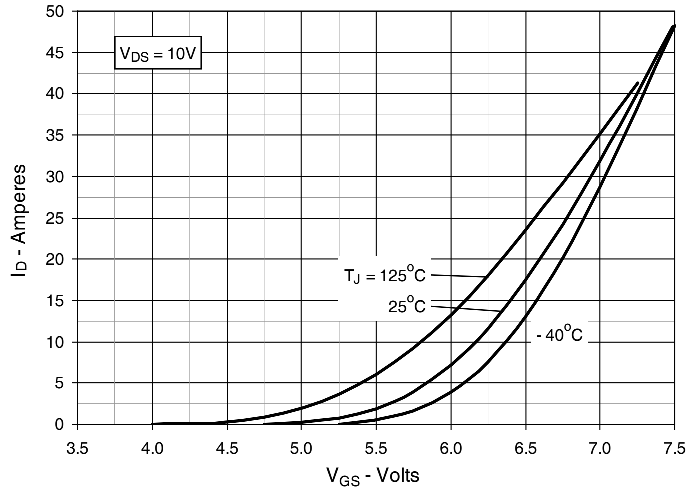


Fig. 8. Transconductance

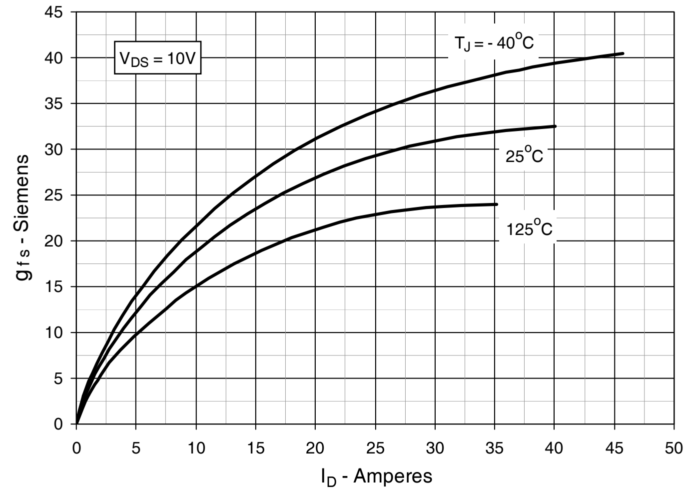


Fig. 9. Forward Voltage Drop of Intrinsic Diode

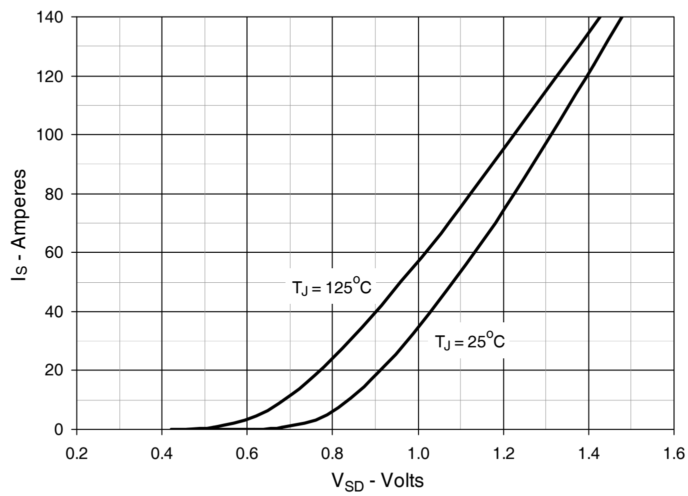


Fig. 10. Gate Charge

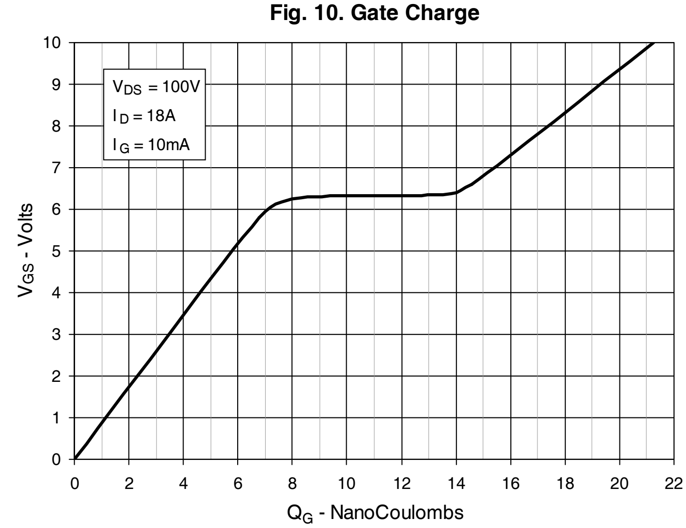


Fig. 11. Capacitance

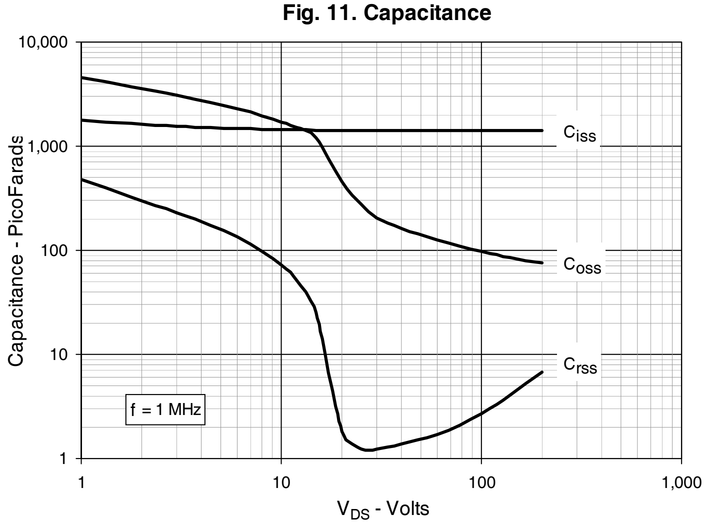


Fig. 12. Output Capacitance Stored Energy

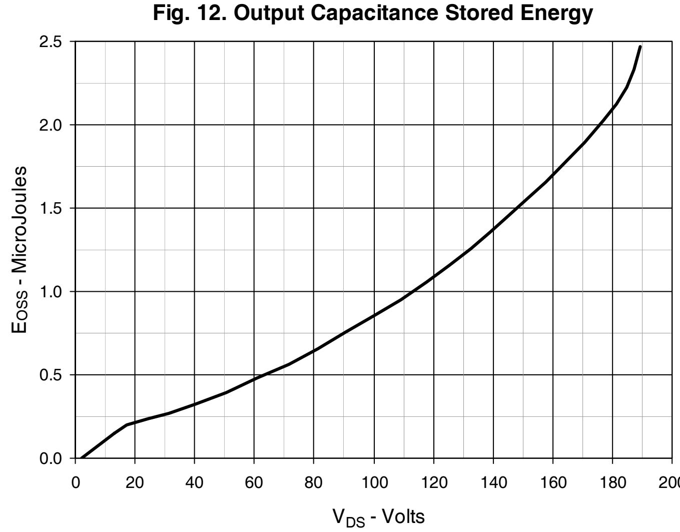


Fig. 13. Forward-Bias Safe Operating Area

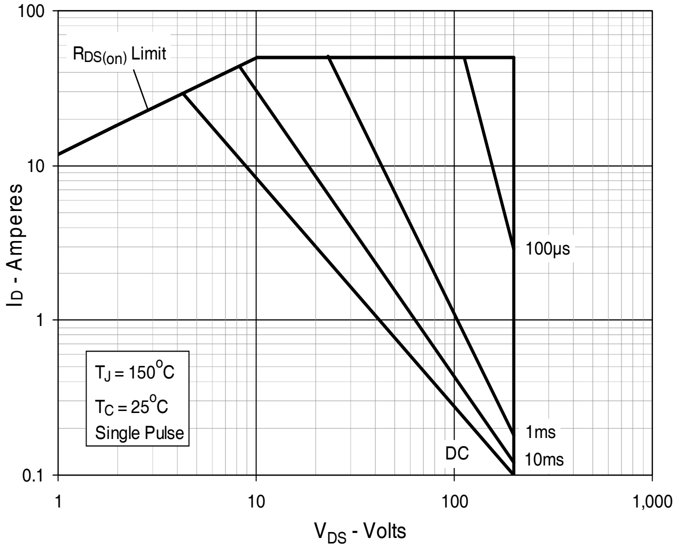


Fig. 14. Maximum Transient Thermal Impedance